

#### **DUAL 20V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BVDSS	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	$25m\Omega @ V_{GS} = 4.5V$	6.0A
20V	31mΩ @ Vgs = 2.5V	5.1A

### **Description**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Battery Management Application
- Power Management Functions
- DC-DC Converters

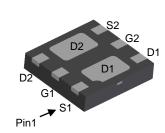
#### **Features**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

#### **Mechanical Data**

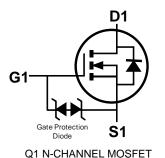
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

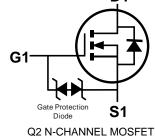




U-DFN2020-6 (Type B)

Bottom View





**D1** 

Internal Schematic

### Ordering Information (Note 4)

Part Number	Case	Packaging		
DMN2025UFDB-7	U-DFN2020-6 (Type B)	3000/Tape & Reel		
DMN2025UFDB-13	U-DFN2020-6 (Type B)	10000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



# **Marking Information**

Site 1



O5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Kev

Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Е		Н	- 1	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



O5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = week 27; z represents week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Kev

Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	7		0	1	2	3	4	5	6	7	8	9
Week		1-	26			27	-52			5	3	
Code		Α	-Z			a	Z			Ž	<u> </u>	
Internal Code	Sur	1	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	V	Х		Υ		Z



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage	Gate-Source Voltage				
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	l <sub>D</sub>	6.0 4.8	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	5)		I <sub>DM</sub>	35	Α
Continuous Source-Drain Diode Current	Is	2	Α		
Avalanche Current (Note 7) L = 0.1mH	las	12	А		
Avalanche Energy (Note 7) L = 0.1mH			Eas	8	mJ

# **Thermal Characteristics**

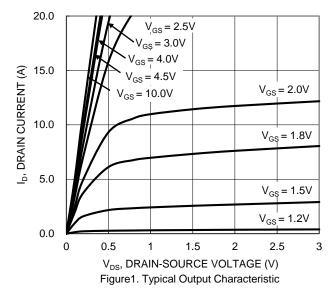
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	170	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	98	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rejc	22	*C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	l	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	-	1	μΑ	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5		1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	D		18.5	25	mΩ	VGS = 4.5V, ID = 4A
Static Dialif-Source Off-Resistance	RDS(ON)		26	31	11177	Vgs = 2.5V, ID = 4A
Diode Forward Voltage	Vsp	_	0.7	1.2	V	Vgs = 0V, Is = 5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	486	_		101/11/
Output Capacitance	Coss	_	92		pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	77	_		1 - 1.000112
Gate Resistance	Rg	_	3.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.9	_		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	12.3	_	nC	\/ 40\/ I- 65A
Gate-Source Charge	Qgs	_	0.8	_	nc	$V_{DS} = 10V, I_{D} = 6.5A$
Gate-Drain Charge	$Q_{gd}$	_	2.2	_		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.4	_		
Turn-On Rise Time	t <sub>R</sub>	_	5.4	_		V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V,
Turn-Off Delay Time	tD(OFF)	_	17.6	_	ns	$R_G = 6\Omega$ , $R_L = 10\Omega$ , $I_D = 1A$
Turn-Off Fall Time	tF	_	9.3	_		
Reverse Recovery Time	t <sub>RR</sub>	_	7.7	_	ns	I <sub>F</sub> = 1A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>		1.5	_	nC	I <sub>F</sub> = 1A, di/dt = 100A/µs

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- Bevice including of the substitute of county 202 copper, with finite square copper
   I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.





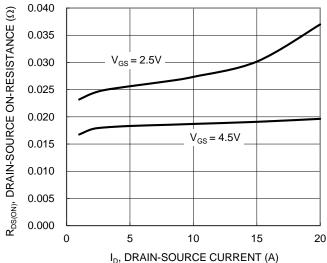


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

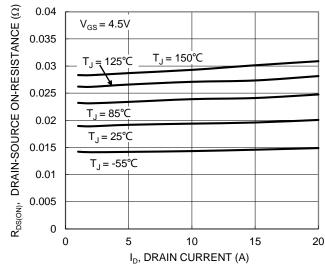
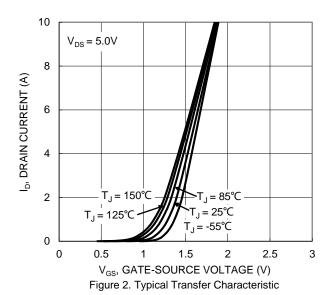


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



0.18
0.18
0.16
0.14
0.12
0.12
0.08
0.08
0.06
0.06
0.004
0.002
0.002

4

2

0

V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

6

8

10

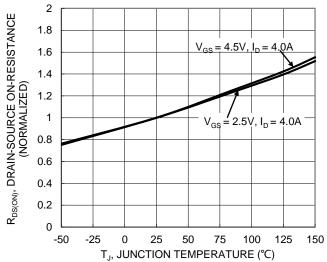


Figure 6. On-Resistance Variation with Temperature



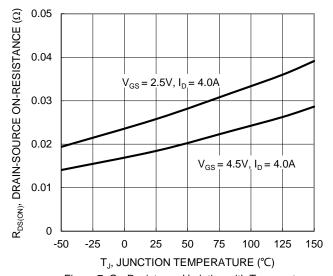


Figure 7. On-Resistance Variation with Temperature

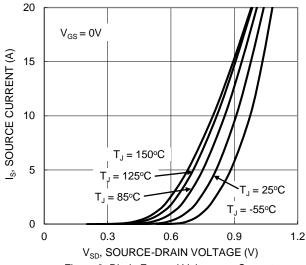
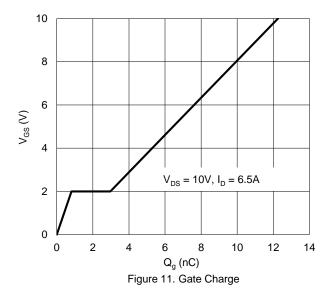


Figure 9. Diode Forward Voltage vs. Current



1.2  $V_{GS(TH)}$ , GATE THRESHOLD VOLTAGE (V) 0.9  $I_D = 1mA$ 0.6  $I_{D} = 250 \mu A$ 0.3 0 -50 -25 25 50 75 100 125 150 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature

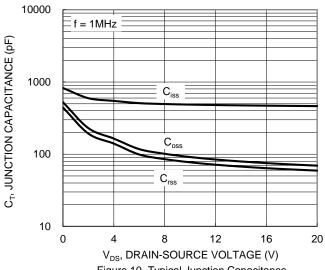


Figure 10. Typical Junction Capacitance

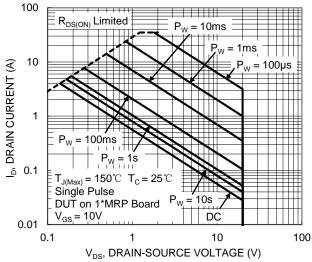


Figure 12. SOA, Safe Operation Area



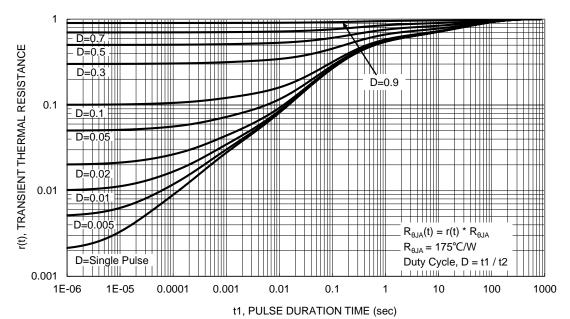


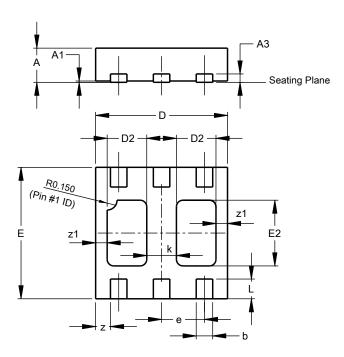
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type B)

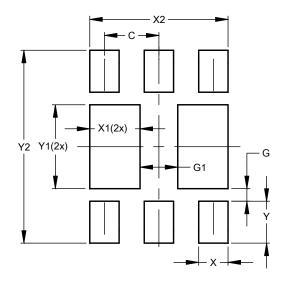


		2020-6					
Dim	Min	Type B Min Max					
Α	0.545	0.605	0.575				
A1	0.00	0.05	0.02				
А3	-	-	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
D2	0.50	0.70	0.60				
е	-	-	0.65				
Е	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
k	-	-	0.45				
L	0.25	0.35	0.30				
Z	-	-	0.225				
z1	-	-	0.175				
All	Dimens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Υ	0.500
Y1	1.000
Y2	2.300



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